



Figure 1: SEM micrograph of the cross section of SiNW with height of 28 nm and width of 30 nm.

Table 1: The Results of the SiNW Width Values

sample	a-Si:H thickness (nm)	Mandrel	Etching process	SiNW width (nm)	Lateral anisotropic etching of a-Si:H
#1	150	Al	RIE	30	yes
#2			ECR	45	
#3	60		ICP	60	no
#4	150	SiN _x	ECR	50	yes
#5				100	yes
#6		Photoresist	ICP	143	no
#7				RIE	110